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2SC2383

NPN Silicon Plastic-Encapsulate Transistor

Features

- Capable of 0.9Watts of Power Dissipation.
- Collector-current 1.0A
- Collector-base Voltage 160V
- Operating and storage junction temperature range: -55°C to +150°C

Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
OFF CHARACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ($I_C=10mA$, $I_B=0$)	160		Vdc
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_C=100\mu A$, $I_E=0$)	160		Vdc
$V_{(BR)EBO}$	Emitter-Base Voltage ($I_C=10mA$, $I_B=0$)	6.0		Vdc
I_{CBO}	Collector Cutoff Current ($V_{CB}=150Vdc$, $I_E=0$)		1.0	μA
I_{CER}	Collector Cutoff Current ($V_{CB}=150Vdc$, $R_{EB}=10m\Omega$)		10	μA
I_{EBO}	Emitter Cutoff Current ($V_{EB}=6.0Vdc$, $I_C=0$)		1.0	μA

ON CHARACTERISTICS

$h_{FE(1)}$	DC Current Gain ($I_C=200mA$, $V_{CE}=5.0Vdc$)	60	320	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($I_C=500mA$, $I_B=50mA$)		1.0	Vdc
V_{BE}	Base-Emitter Voltage ($I_C=5.0mA$, $V_{CE}=5.0Vdc$)		0.75	Vdc

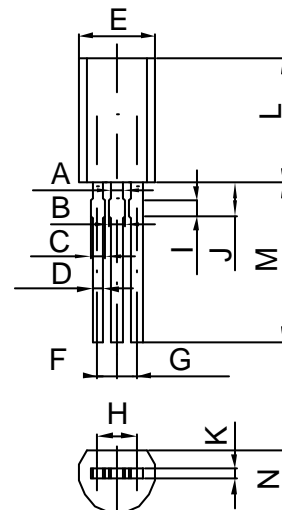
SMALL-SIGNAL CHARACTERISTICS

f_T	Transistor Frequency ($I_C=200mA$, $V_{CE}=5.0Vdc$)	20		MHz
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CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O	Y
Range	60-120	100-200	160-320

TO-92MOD



DIMENSIONS

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	---	.030	---	.750	
B	---	.039	---	1.00	
C	---	.031	---	.80	
D	---	.024	---	0.60	
E	---	.201	---	5.10	
F	.050		1.27		
G	.050		1.27		
H	.100		2.54		
I	.039		1.00		
J	---	.087	---	2.20	
K	---	.024	---	.60	
L	---	.323	---	8.20	
M	---	.413	---	10.50	
N	---	.161	---	4.10	